

Pavel Yu Bokov

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6709213/publications.pdf>

Version: 2024-02-01

24
papers

65
citations

1684188

5
h-index

1720034

7
g-index

24
all docs

24
docs citations

24
times ranked

67
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Study of built-in electric field in active region of GaN/InGaN/AlGaN LEDs by electroreflectance spectroscopy. <i>Solid-State Electronics</i> , 2017, 130, 45-48. | 1.4 | 2 |
| 2 | Electroreflectance spectra from multiple InGaN/GaN quantum wells in the nonuniform electric field of a p-n junction. <i>Semiconductors</i> , 2017, 51, 189-192. | 0.5 | 1 |
| 3 | Raman scattering in InP doped by Be ⁺ -ion implantation. <i>Semiconductors</i> , 2017, 51, 168-172. | 0.5 | 1 |
| 4 | Unintentional indium incorporation into barriers of InGaN/GaN multiple quantum wells studied by photoreflectance and photoluminescence excitation spectroscopy. <i>Journal of Applied Physics</i> , 2016, 120, . | 2.5 | 5 |
| 5 | Characterization of the spatial inhomogeneity of heterointerfaces in GaAs/AlGaAs quantum wells by photoreflectance spectroscopy. <i>Semiconductors</i> , 2015, 49, 1202-1206. | 0.5 | 1 |
| 6 | Electrical and optical properties of near-surface AlGaAs/InGaAs/AlGaAs quantum wells with different quantum-well depths. <i>Semiconductors</i> , 2013, 47, 1203-1208. | 0.5 | 8 |
| 7 | Linear Electro-Optic Effect in Electroreflectance Spectra of AlGaN/InGaN/GaN Light Emitting Diodes Structures. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JK11. | 1.5 | 0 |
| 8 | Impact of AlN Spacer on Metal-Semiconductor-Metal Pt-InAlGaN/GaN Heterostructures for Ultraviolet Detection. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JK04. | 1.5 | 2 |
| 9 | The difference between reflectance and electroreflectance spectra of AlGaN/GaN/InGaN LED structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 818-821. | 0.8 | 3 |
| 10 | Photoreflectance spectroscopy of delta-doped GaAs layers. <i>Inorganic Materials</i> , 2011, 47, 455-458. | 0.8 | 2 |
| 11 | Photoreflectance spectroscopy of electron-hole states in a graded-width GaAs/InGaAs/GaAs quantum well. <i>Semiconductors</i> , 2011, 45, 320-324. | 0.5 | 1 |
| 12 | Interference effects in the electroreflectance and electroluminescence spectra of InGaN/AlGaN/GaN light-emitting-diode heterostructures. <i>Semiconductors</i> , 2010, 44, 1090-1095. | 0.5 | 8 |
| 13 | Piezoelectric field compensation in the InGaN quantum wells of GaN/InGaN/AlGaN LEDs structures: electroreflectance experiment. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1863-1865. | 0.8 | 3 |
| 14 | Electroreflectance diagnostics of InGaN/AlGaN/GaN based LEDs structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 2852-2854. | 0.8 | 1 |
| 15 | Photoreflectance study of plasma-etched semi-insulating GaAs substrates treated. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2008, 72, 941-943. | 0.6 | 0 |
| 16 | A Role of the Built-in Piezoelectric Field in InGaN/AlGaN/GaN Multiple Quantum Wells in the Electroreflectance Experiments. <i>Materials Research Society Symposia Proceedings</i> , 2007, 1040, 1. | 0.1 | 0 |
| 17 | Determination of the carrier concentration in doped n-GaAs layers by Raman and light reflection spectroscopies. <i>Optics and Spectroscopy (English Translation of Optika i Spektroskopiya)</i> , 2007, 102, 712-716. | 0.6 | 2 |
| 18 | Electroreflectance spectra of InGaN/AlGaN/GaN quantum-well heterostructures. <i>Semiconductors</i> , 2007, 41, 1060-1066. | 0.5 | 9 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Interband optical transitions in GaAs modulation-doped quantum wells: photoreflectance experiment and self-consistent calculations. Semiconductor Science and Technology, 2006, 21, 462-466. | 2.0 | 4 |
| 20 | Electroreflectance Spectra of InGaN/AlGaIn/GaN p-n-Heterostructures. Materials Research Society Symposia Proceedings, 2006, 955, 1. | 0.1 | 0 |
| 21 | Photoreflexion Studies of the Dopant Activation in InP Implanted with Be ⁺ Ions. Semiconductors, 2005, 39, 174. | 0.5 | 2 |
| 22 | Photoreflexion studies of band offsets at the heterojunction in strained short-period GaAs/GaAsP superlattices. Semiconductors, 2004, 38, 1384-1389. | 0.5 | 4 |
| 23 | Investigation of electronic transitions in coupled-quantum-well structures with a built-in electric field by photoreflectance spectroscopy. Semiconductors, 2003, 37, 77-81. | 0.5 | 0 |
| 24 | Study of the effects of size quantization in coupled Al _x Ga _{1-x} As/GaAs/Al _x Ga _{1-x} As quantum wells by means of photoreflectance spectroscopy. Optics and Spectroscopy (English Translation of Optika i Tj ETQq0 0 0 rgrB /Overlock 10 Tf 5 | | |